

R1LV0216BSB

2Mb Advanced LPSRAM (128k word x 16bit)

R10DS0273EJ0101
Rev.1.01
2020.2.20

Description

The R1LV0216BSB is a family of low voltage 2-Mbit static RAMs organized as 131,072-word by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies. The R1LV0216BSB has realized higher density, higher performance and low power consumption. The R1LV0216BSB is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives. The R1LV0216BSB has been packaged in 44-pin TSOP.

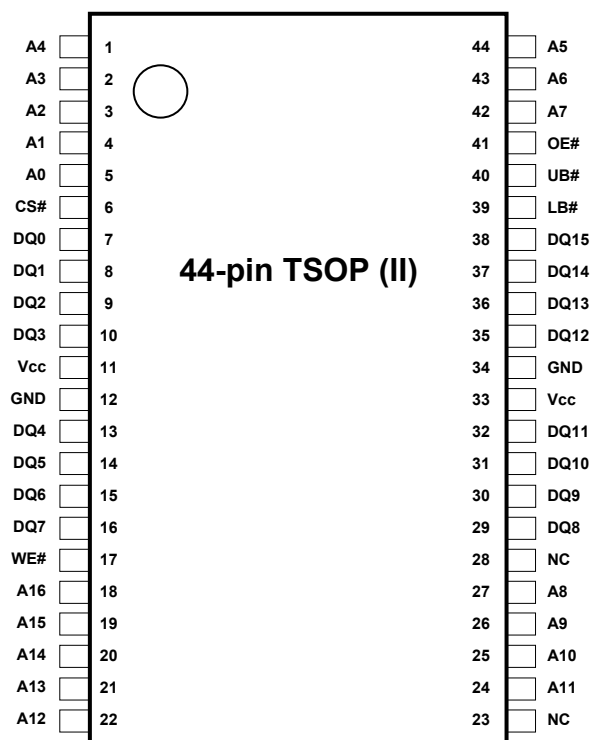
Features

- Single 2.7V~3.6V power supply
- Small stand-by current: 1μA (3.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS#, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

Ordering Information

Orderable part name	Access time	Temperature range	Package	Shipping container
R1LV0216BSB-5SI#B1	55 ns	-40 ~ +85°C	400-mil 44pin plastic TSOP (II)	Tray
R1LV0216BSB-5SI#S1				Embossed tape

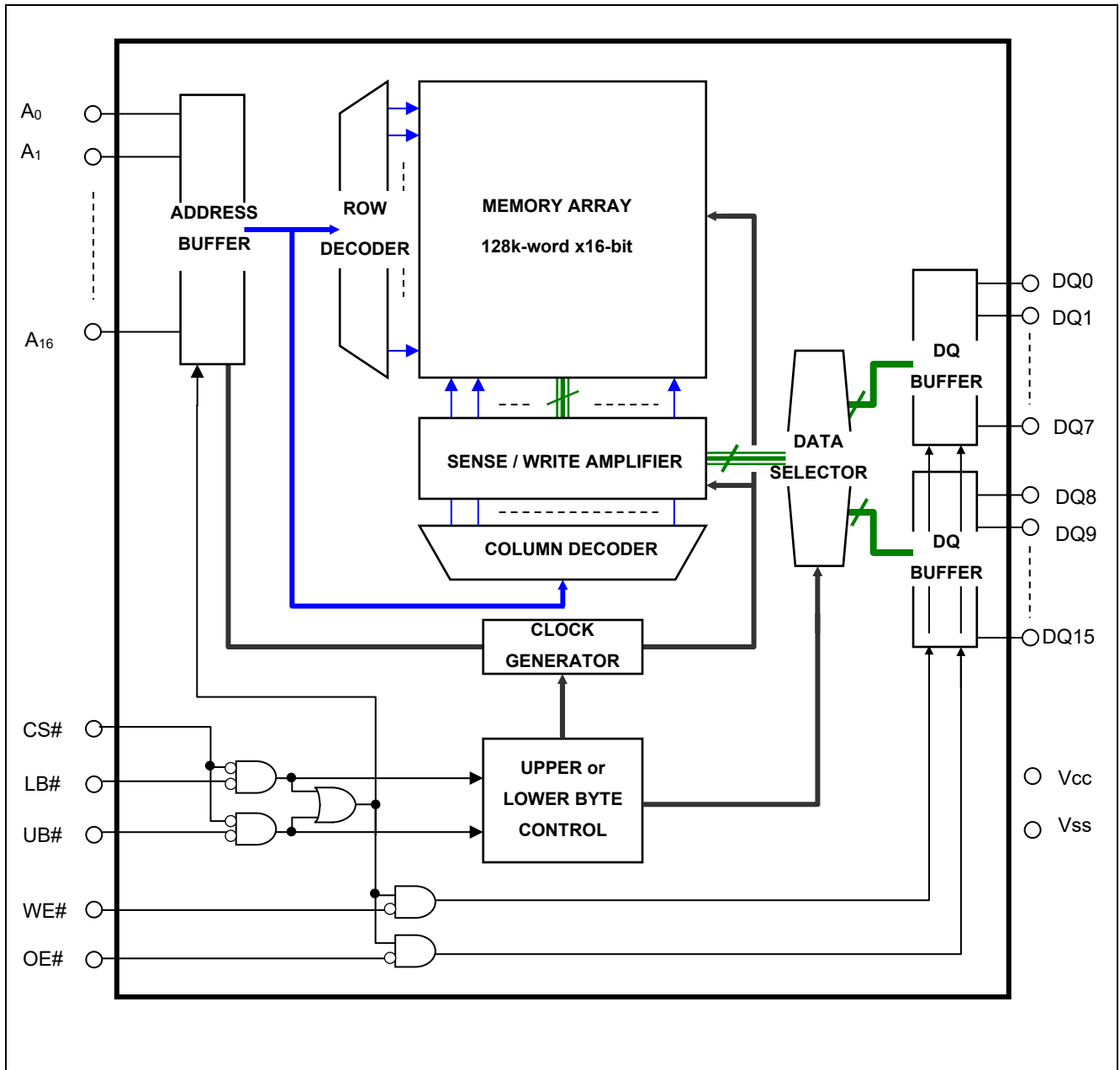
Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss (GND)	Ground
A0 to A16	Address input
DQ0 to DQ15	Data input/output
CS#	Chip select
WE#	Write enable
OE#	Output enable
LB#	Lower byte enable
UB#	Upper byte enable
NC	Non connection

Block Diagram



Operation Table

CS#	LB#	UB#	WE#	OE#	DQ0~7	DQ8~15	Operation
H	X	X	X	X	High-Z	High-Z	Stand-by
X	H	H	X	X	High-Z	High-Z	Stand-by
L	L	H	L	X	Din	High-Z	Write in lower byte
L	L	H	H	L	Dout	High-Z	Read in lower byte
L	L	H	H	H	High-Z	High-Z	Output disable
L	H	L	L	X	High-Z	Din	Write in upper byte
L	H	L	H	L	High-Z	Dout	Read in upper byte
L	H	L	H	H	High-Z	High-Z	Output disable
L	L	L	L	X	Din	Din	Word write
L	L	L	H	L	Dout	Dout	Word read
L	L	L	H	H	High-Z	High-Z	Output disable

Note 1. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

Absolute Maximum

Parameter	Symbol	Value	unit
Power supply voltage relative to Vss	Vcc	-0.5 to +4.6	V
Terminal voltage on any pin relative to Vss	V_T	-0.5 ¹ to Vcc+0.5 ²	V
Power dissipation	P_T	0.7	W
Operation temperature	Topr	-40 to +85	°C
Storage temperature range	Tstg	-65 to 150	°C
Storage temperature range under bias	Tbias	-40 to +85	°C

Note 1. -3.0V for pulse ≤ 30 ns (full width at half maximum)
 2. Maximum voltage is +4.6V.

DC Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note
Supply voltage	V _{CC}	2.7	3.0	3.6	V	
	V _{SS}	0	0	0	V	
Input high voltage	V _{IH}	2.2	-	V _{CC} +0.3	V	
Input low voltage	V _{IL}	-0.3	-	0.6	V	1
Ambient temperature range	T _a	-40	-	+85	°C	

Note 1. -3.0V for pulse ≤ 30ns (full width at half maximum)

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Input leakage current	I _{LI}	-	-	1	μA	Vin = Vss to Vcc	
Output leakage current	I _{LO}	-	-	1	μA	CS# = LB# = UB# = VIH or OE# =VIH, VI/O =Vss to Vcc	
Average operating current	I _{CC1}	-	15	25	mA	Min. cycle, duty =100%, II/O = 0mA, CS# =VIL, Others = VIH/VIL	
	I _{CC2}	-	2	5	mA	Cycle =1μs, duty =100%, II/O = 0mA, CS# ≤ 0.2V, VIH ≥ Vcc-0.2V, VIL ≤ 0.2V	
Standby current	I _{SB}	-	-	0.5	mA	(1) CS# = VIH, Others =VIH/VIL or (2) LB# = UB# = VIH, Others =VIH/VIL	
Standby current	I _{SB1}	-	1*1	2	μA	~+25°C	Vin = Vss to Vcc, (1) CS# ≥ Vcc-0.2V or (2) LB# = UB# ≥ Vcc-0.2V, CS# ≤ 0.2V
		-	-	3	μA	~+40°C	
		-	-	8	μA	~+70°C	
		-	-	10	μA	~+85°C	
Output high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -0.5mA	
	V _{OH2}	Vcc - 0.5	-	-	V	I _{OH} = -0.05mA	
Output low voltage	V _{OL}	-	-	0.4	V	I _{OL} = 2mA	

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 25°C), and not 100% tested.

Capacitance

(V_{CC} = 2.7V ~ 3.6V, f = 1MHz, T_a = -40 ~ +85°C)

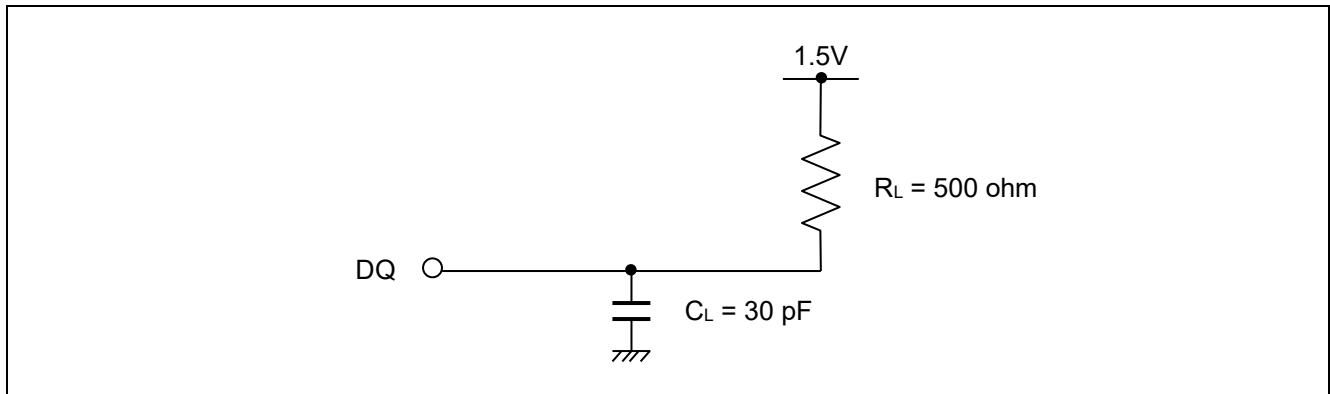
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C _{in}	-	-	8	pF	V _{in} = 0V	1
Input / output capacitance	C _{I/O}	-	-	10	pF	V _{I/O} = 0V	1

Note 1. This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions ($V_{CC} = 2.7V \sim 3.6V$, $T_a = -40 \sim +85^{\circ}C$)

- Input pulse levels: $V_{IL} = 0.4V$, $V_{IH} = 2.4V$
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.5V
- Output load: See figures (Including scope and jig)



Read Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Read cycle time	t _{RC}	55	-	ns	
Address access time	t _{AA}	-	55	ns	
Chip select access time	t _{ACS}	-	55	ns	
Output enable to output valid	t _{OE}	-	30	ns	
Output hold from address change	t _{OH}	10	-	ns	
LB#, UB# access time	t _{BA}	-	55	ns	
Chip select to output in low-Z	t _{CLZ}	10	-	ns	2,3
LB#, UB# enable to low-Z	t _{BLZ}	10	-	ns	2,3
Output enable to output in low-Z	t _{OLZ}	5	-	ns	2,3
Chip deselect to output in high-Z	t _{CHZ}	0	20	ns	1,2,3
LB#, UB# disable to high-Z	t _{BHZ}	0	20	ns	1,2,3
Output disable to output in high-Z	t _{OHZ}	0	20	ns	1,2,3

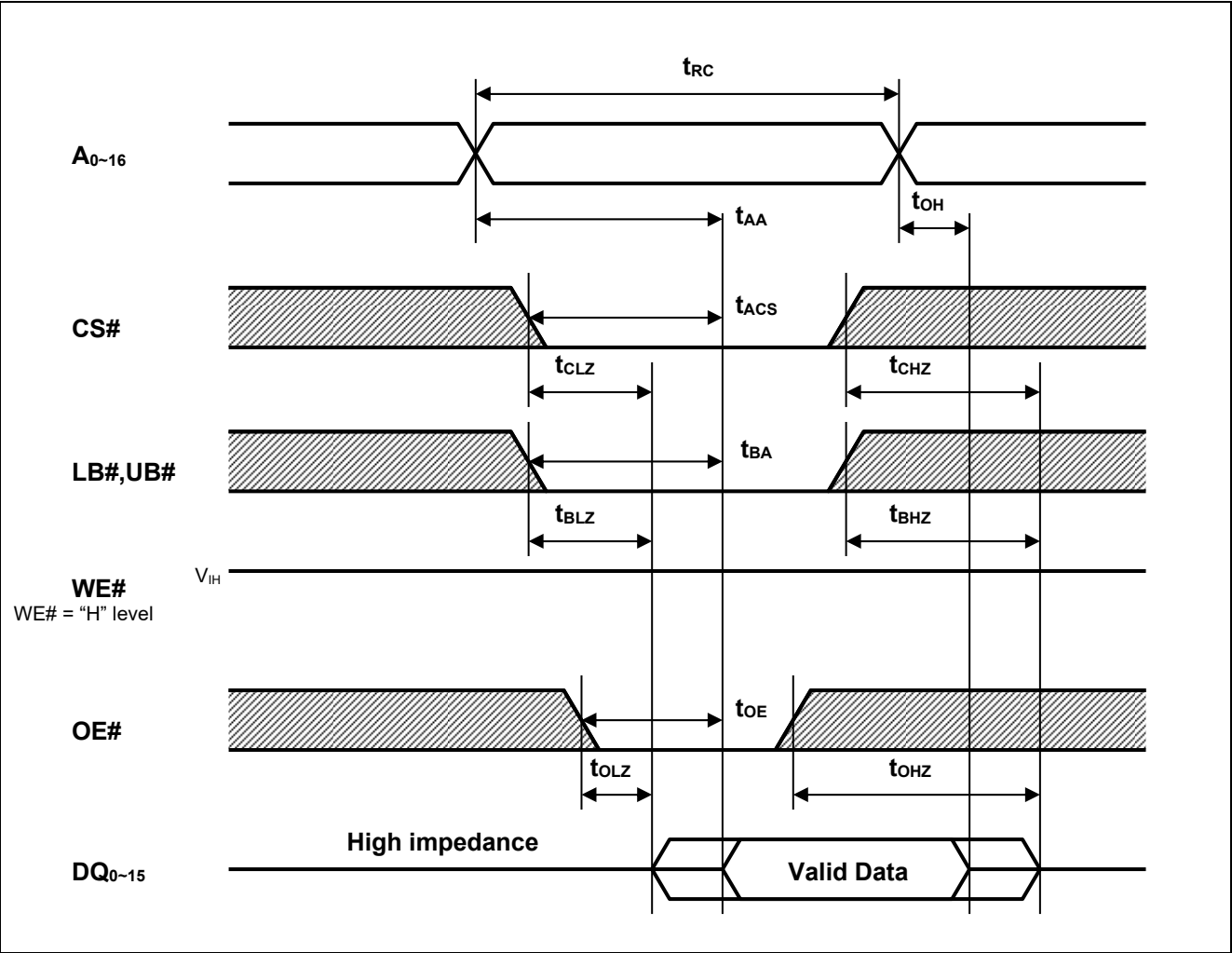
Write Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Write cycle time	t _{WC}	55	-	ns	
Address valid to end of write	t _{AW}	50	-	ns	
Chip select to end of write	t _{CW}	50	-	ns	5
Write pulse width	t _{WP}	45	-	ns	4
LB#, UB# valid to end of write	t _{BW}	50	-	ns	
Address setup time	t _{AS}	0	-	ns	6
Write recovery time	t _{WR}	0	-	ns	7
Data to write time overlap	t _{DW}	25	-	ns	
Data hold from write time	t _{DH}	0	-	ns	
Output enable from end of write	t _{OW}	5	-	ns	2
Output disable to output in high-Z	t _{OHZ}	0	20	ns	1,2
Write to output in high-Z	t _{WHZ}	0	20	ns	1,2

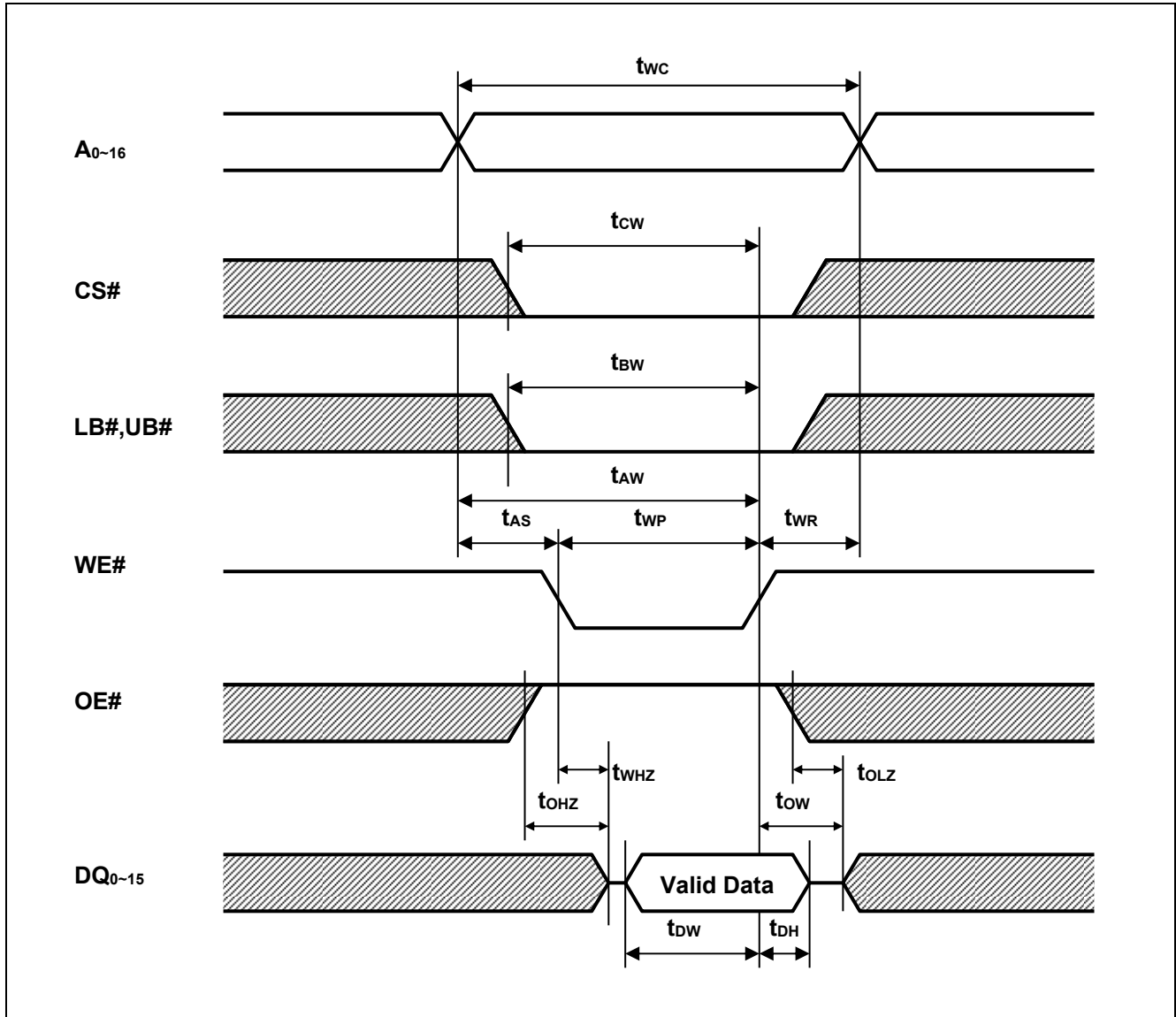
- Note
1. t_{CHZ}, t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 2. This parameter is sampled and not 100% tested.
 3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
 4. A write occurs during the overlap of a low CS#, a low WE# and a low LB# or a low UB#.
A write begins at the latest transition among CS# going low, WE# going low and LB# going low or UB# going low.
A write ends at the earliest transition among CS# going high, WE# going high and LB# going high or UB# going high.
t_{WP} is measured from the beginning of write to the end of write.
 5. t_{CW} is measured from the later of CS# going low to end of write.
 6. t_{AS} is measured the address valid to the beginning of write.
 7. t_{WR} is measured from the earliest of CS#, WE#, LB# or UB# going high to the end of write cycle.
 8. Don't apply inverted phase signal externally when DQ pin is output mode.

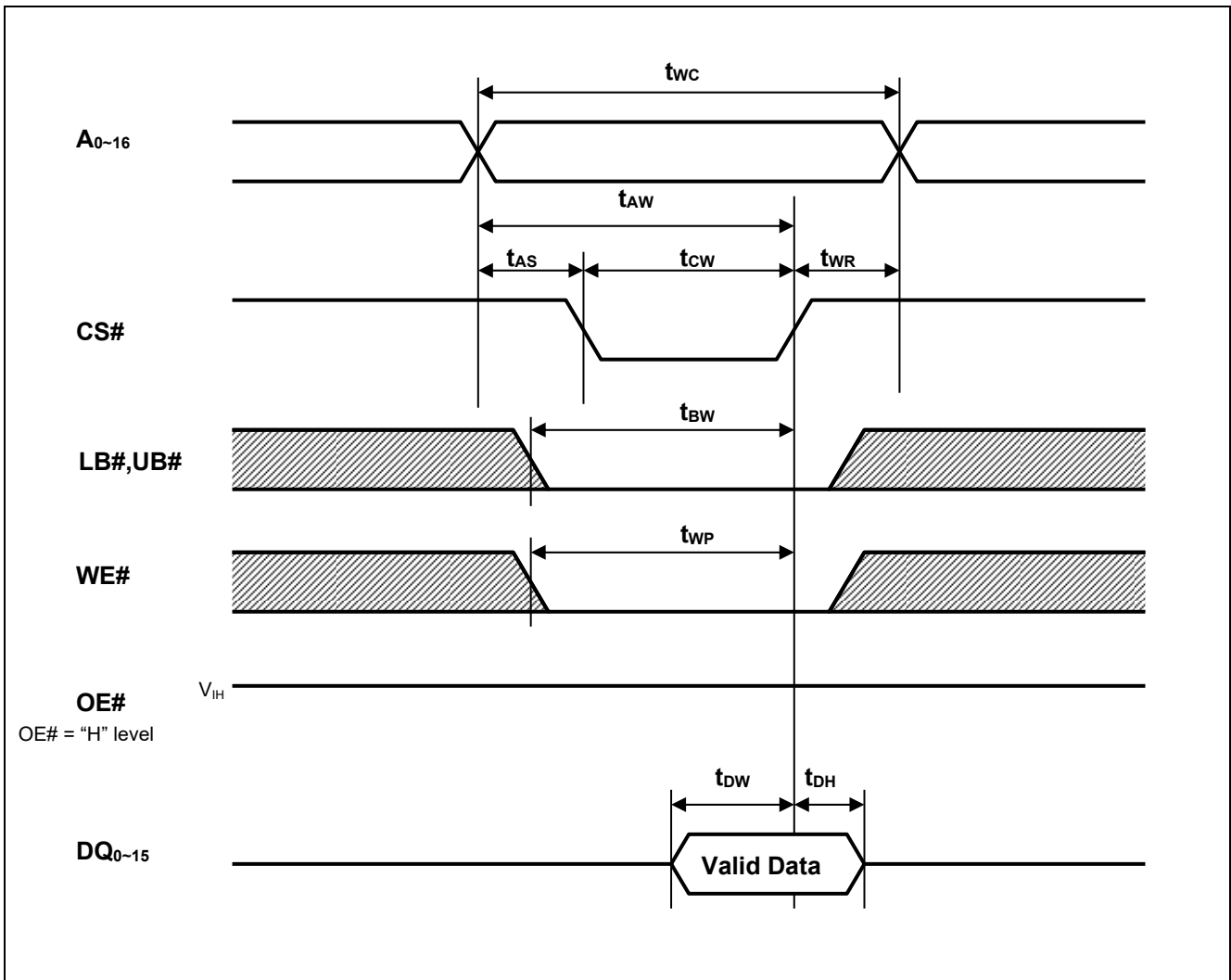
Timing Waveforms

Read Cycle

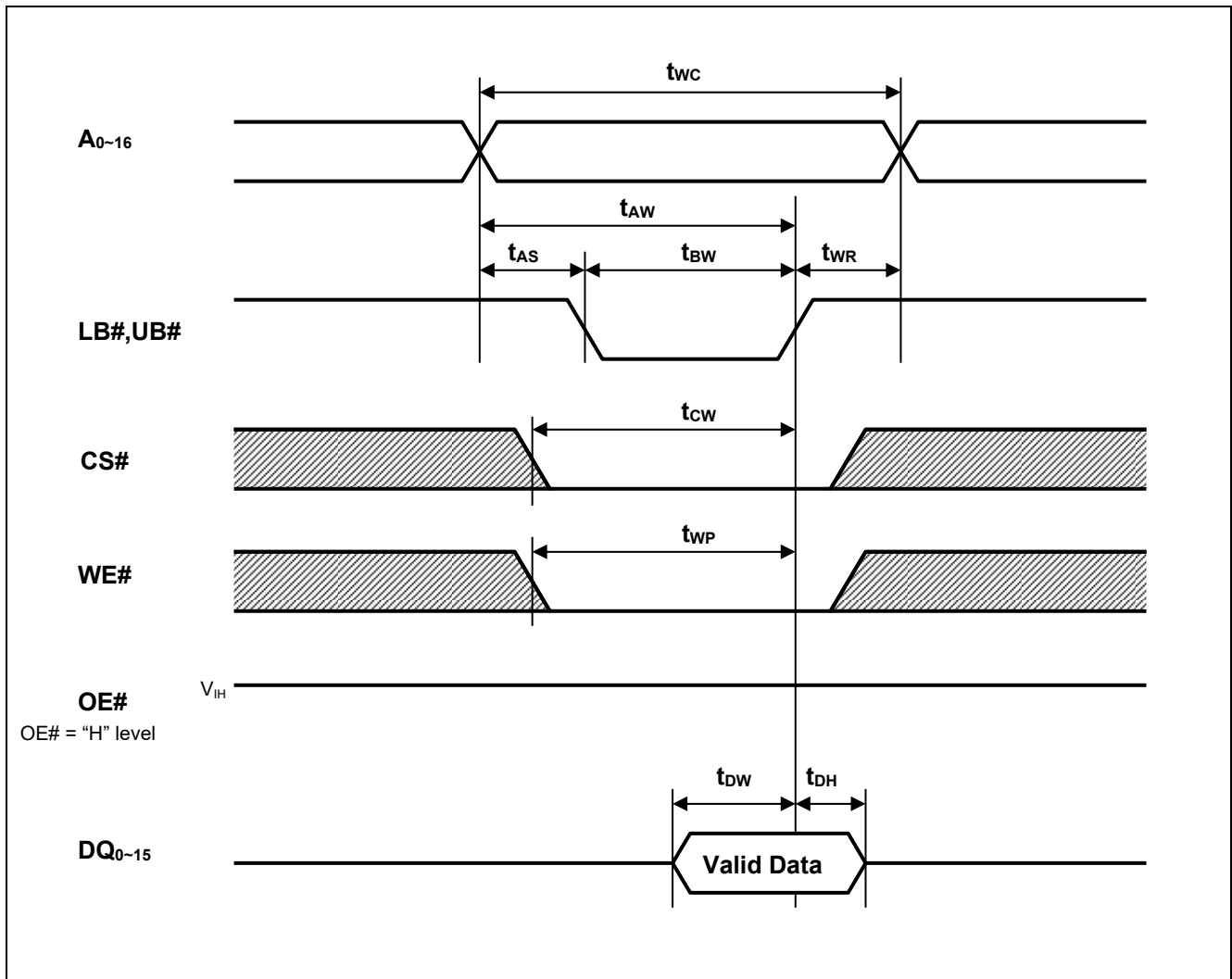


Write Cycle (1) (WE# CLOCK)



Write Cycle (2) (CS# CLOCK)

Write Cycle (3) (LB#, UB# CLOCK)



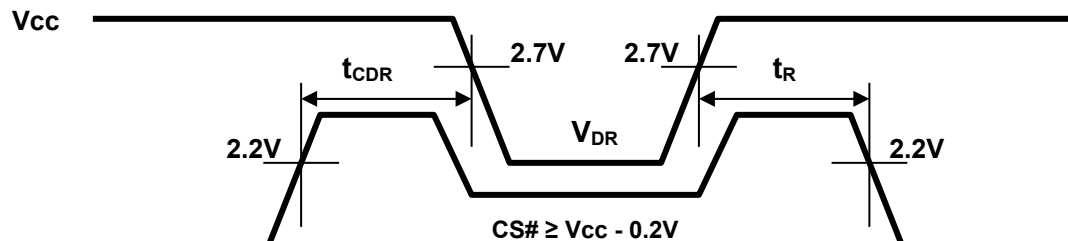
Low Vcc Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions ^{*2}	
V _{CC} for data retention	V _{DR}	2.0	-	3.6	V	Vin ≥ 0V, (1) CS# ≥ Vcc-0.2V or (2) LB# = UB# ≥ Vcc-0.2V, CS# ≤ 0.2V	
Data retention current	I _{CCDR}	-	1 ^{*1}	2	μA	~+25°C	Vcc=3.0V, Vin ≥ 0V, (1) CS# ≥ Vcc-0.2V or (2) LB# = UB# ≥ Vcc-0.2V, CS# ≤ 0.2V
		-	-	3	μA	~+40°C	
		-	-	8	μA	~+70°C	
		-	-	10	μA	~+85°C	
Chip deselect time to data retention	t _{CDR}	0	-	-	ns	See retention waveform.	
Operation recovery time	t _R	5	-	-	ms		

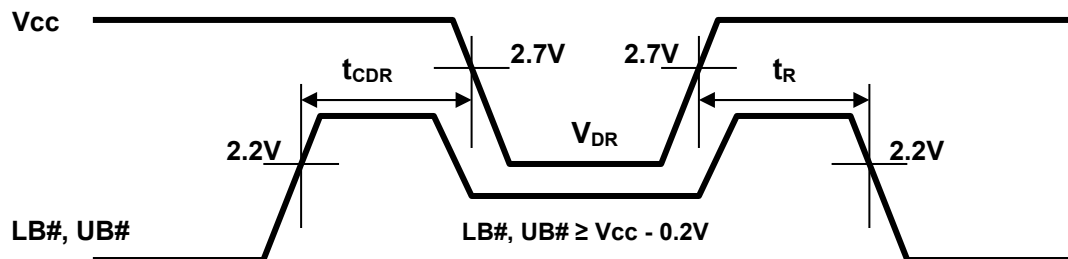
- Note
1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 25°C), and not 100% tested.
 2. CS# controls address buffer, WE# buffer, OE# buffer, LB# buffer, UB# buffer and Din buffer. If CS# controls data retention mode, V_{in} levels (address, WE#, OE#, LB#, UB#, DQ) can be in the high impedance state.

Low Vcc Data Retention Timing Waveforms

(1) CS# Controlled



(2) LB#, UB# Controlled



Revision History	R1LV0216BSB Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	2017.1.27	-	First Edition issued
1.01	2020.2.20	Last page	Updated the Notice to the latest version

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